

Maryam Amirhoseiny

List of Publications by Year in descending order

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27

papers

200

citations

1040056

9

h-index

1058476

14

g-index

27

all docs

27

docs citations

27

times ranked

142

citing authors

#	ARTICLE	IF	CITATIONS
1	The effect of AlGaN bulk and AlGaN/GaN superlattice cladding layers on performance characteristics of deep violet InGaN DQW lasers. Vacuum, 2017, 141, 139-143.	3.5	7
2	Synthesis of CuS Nanoparticles by Laser Ablation Method in DMSO Media. Journal of Cluster Science, 2017, 28, 2753-2764.	3.3	21
3	Performance characteristics of deep violet InGaN DQW lasers based on different compliance layers. Optik, 2017, 131, 194-200.	2.9	2
4	Dependence of output emission wavelength and LD performance on barriers material and thickness. Optik, 2016, 127, 4815-4818.	2.9	2
5	Nanoporous all metallic binder free Sn:Pb composite electrode for high performance supercapacitors. Microelectronic Engineering, 2016, 157, 31-34.	2.4	1
6	Effect of different EBL structures on deep violet InGaN laser diodes performance. Optics and Laser Technology, 2016, 76, 106-112.	4.6	29
7	Carbon nanotube-based supercapacitors using low cost collectors. Modern Physics Letters B, 2016, 30, 1550272.	1.9	1
8	INFLUENCE OF WAVEGUIDE LAYERS ON DEEP VIOLET <i>InGaN</i> DQW LASERS PERFORMANCE. Surface Review and Letters, 2015, 22, 1550051.	1.1	0
9	Effect of deposition conditions on properties of nitrogen rich-InN nanostructures grown on anisotropic Si (110). Materials Science in Semiconductor Processing, 2015, 35, 216-221.	4.0	8
10	A SIMPLE METHOD TO PREPARE NANOPOROUS Sn:Pb COMPOSITE METAL FOAM. Surface Review and Letters, 2015, 22, 1550034.	1.1	0
11	Effect of QW thickness and numbers on performance characteristics of deep violet InGaN MQW lasers. International Journal of Modern Physics B, 2015, 29, 1550081.	2.0	5
12	Doping effects in p- and n-type layers of 390-nm <i>InGaN</i> DQW lasers. International Journal of Modern Physics B, 2015, 29, 1550118.	2.0	0
13	Effect of annealing temperature on IR-detectors based on InN nanostructures. Vacuum, 2014, 106, 46-48.	3.5	13
14	Photoluminescence spectra of nitrogen-rich InN thin films grown on Si(110) and photoelectrochemical etched Si(110). Vacuum, 2014, 101, 217-220.	3.5	12
15	Synthesis of nanocrystalline In ₂ O ₃ on different Si substrates at wet oxidation environment. Optik, 2013, 124, 2679-2681.	2.9	6
16	Comparative study on structural and optical properties of nitrogen rich InN on Si(110) and 6H-SiC. Surface Engineering, 2013, 29, 561-565.	2.2	11
17	Growth of InN thin films on different Si substrates at ambient temperature. Microelectronics International, 2013, 30, 63-67.	0.6	8
18	Fabrication of InN based photodetector using porous silicon buffer layer. Surface Engineering, 2013, 29, 772-777.	2.2	15

#	ARTICLE	IF	CITATIONS
19	STRUCTURE AND OPTICAL PROPERTIES OF InN THIN FILM GROWN ON SiC BY REACTIVE RF MAGNETRON SPUTTERING. <i>Surface Review and Letters</i> , 2013, 20, 1350008.	1.1	9
20	InN PHOTOCONDUCTORS ON DIFFERENT ORIENTATIONS OF Si SUBSTRATES. <i>International Journal of Modern Physics B</i> , 2012, 26, 1250137.	2.0	9
21	Reactive Sputtering Growth and Characterizations of InN Thin Films on Si Substrates. <i>Advanced Materials Research</i> , 2012, 545, 290-293.	0.3	0
22	Optical properties of photo-electrochemical etching of anisotropic silicon (110). <i>IEICE Electronics Express</i> , 2012, 9, 752-757.	0.8	6
23	Effects of Cavity Length on Optical Characteristics of Deep Violet InGaN DQW Lasers. <i>Advanced Materials Research</i> , 2012, 626, 605-609.	0.3	1
24	EFFECT OF CURRENT DENSITY ON OPTICAL PROPERTIES OF ANISOTROPIC PHOTOELECTROCHEMICAL ETCHED SILICON (110). <i>Modern Physics Letters B</i> , 2012, 26, 1250131.	1.9	5
25	Characterizations of InN Thin Films Grown on Si (110) Substrate by Reactive Sputtering. <i>Journal of Nanomaterials</i> , 2011, 2011, 1-7.	2.7	26
26	Induced magnetic anisotropy in Fe0.7Co0.3fine particles. <i>Journal Physics D: Applied Physics</i> , 2006, 39, 4925-4929.	2.8	2
27	A Simple Method to Prepare Indium Oxide Nanoparticles on Si (110). <i>Advanced Materials Research</i> , 0, 620, 193-197.	0.3	1